

# FX6ASJ-06

High-Speed Switching Use Pch Power MOS FET

REJ03G1437-0200 (Previous: MEJ02G0272-0101)

> Rev.2.00 Aug 07, 2006

#### **Features**

• Drive voltage: 4 V

•  $V_{DSS} : -60 \text{ V}$ 

•  $r_{DS(ON) \, (max)}$ : 0.21  $\Omega$ 

•  $I_D: -6 A$ 

• Integrated Fast Recovery Diode (TYP.): 50 ns

#### **Outline**

RENESAS Package code: PRSS0004ZA-A (Package name: MP-3A)

1. Gate
2. Drain
3. Source
4. Drain

#### **Applications**

Motor control, Lamp control, Solenoid control, DC-DC converters, etc.

### **Maximum Ratings**

 $(Tc = 25^{\circ}C)$ 

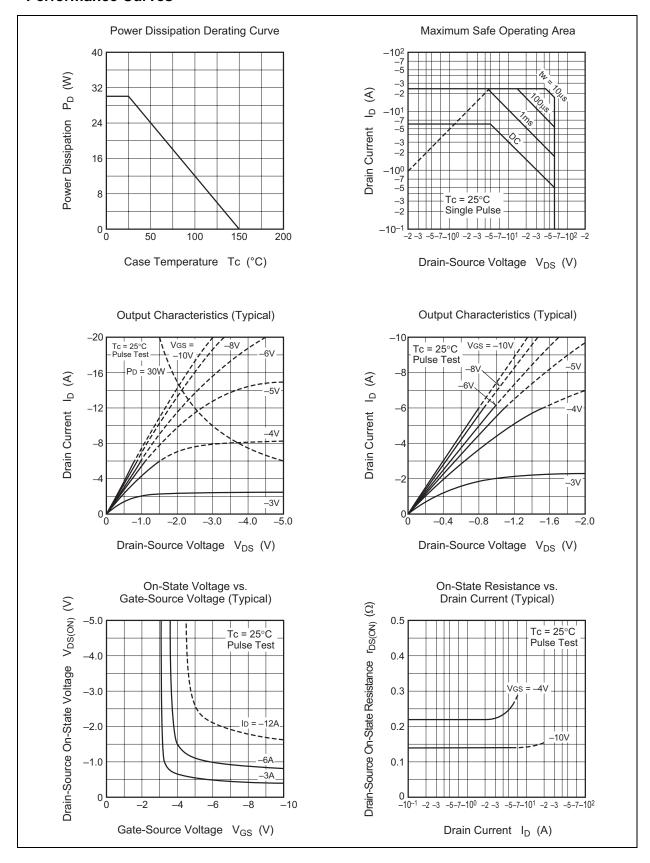
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	$V_{DSS}$	-60	V	V <sub>GS</sub> = 0 V
Gate-source voltage	$V_{GSS}$	±20	V	V <sub>DS</sub> = 0 V
Drain current	I <sub>D</sub>	-6	А	
Drain current (Pulsed)	$I_{DM}$	-24	А	
Avalanche drain current (Pulsed)	I <sub>DA</sub>	-6	А	L = 100 μH
Source current	Is	-6	А	
Source current (Pulsed)	I <sub>SM</sub>	-24	А	
Maximum power dissipation	$P_D$	30	W	
Channel temperature	Tch	- 55 to +150	°C	
Storage temperature	Tstg	- 55 to +150	°C	
Mass		0.32	g	Typical value

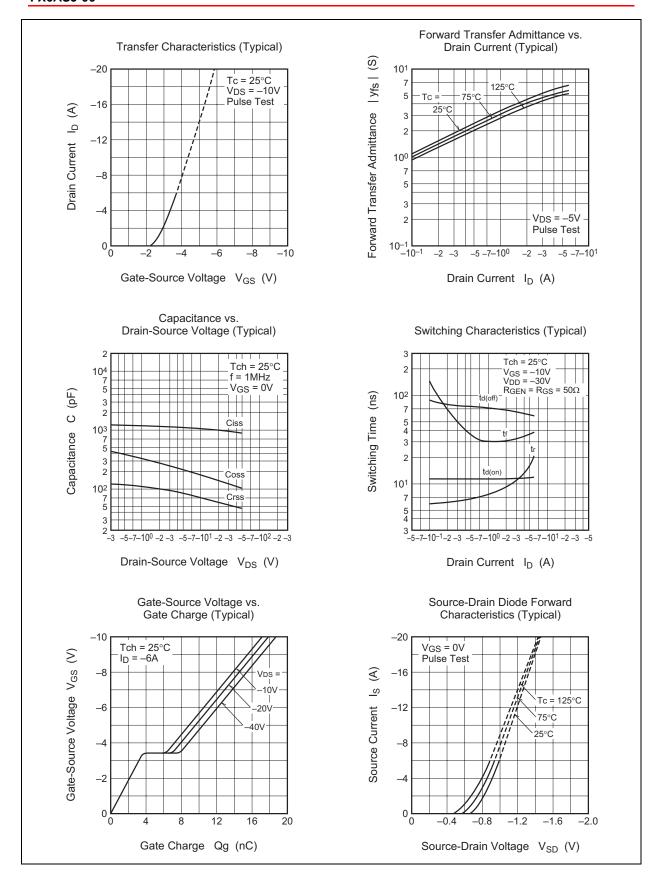
#### **Electrical Characteristics**

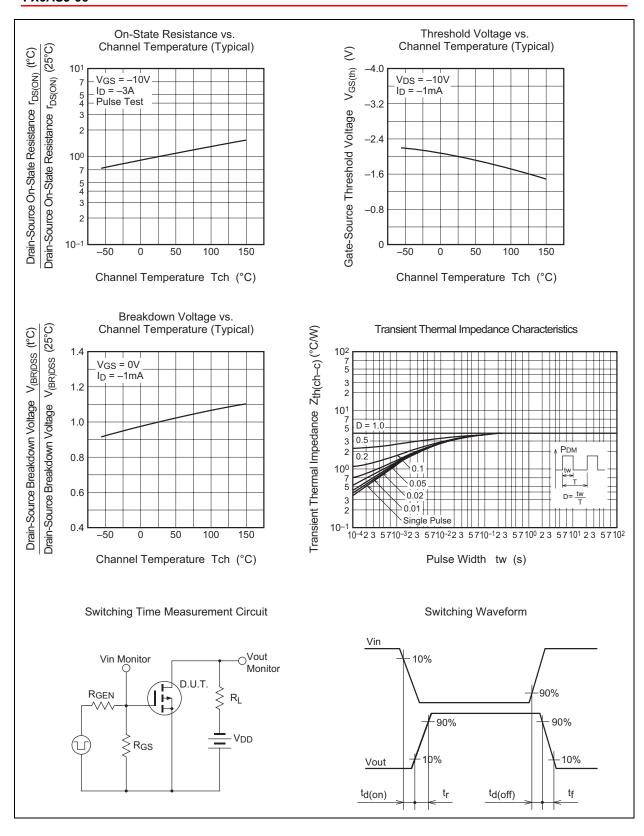
 $(Tch = 25^{\circ}C)$ 

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	-60	_	_	V	$I_D = -1$ mA, $V_{GS} = 0$ V
Gate-source leakage current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Drain-source leakage current	I <sub>DSS</sub>	_	_	-0.1	mA	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$
Gate-source threshold voltage	$V_{GS(th)}$	-1.3	-1.8	-2.3	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Drain-source on-state resistance	r <sub>DS(ON)</sub>	_	0.16	0.21	Ω	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}$
Drain-source on-state resistance	r <sub>DS(ON)</sub>	_	0.27	0.37	Ω	$I_D = -3 \text{ A}, V_{GS} = -4 \text{ V}$
Drain-source on-state voltage	V <sub>DS(ON)</sub>	_	-0.48	-0.63	V	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}$
Forward transfer admittance	y <sub>fs</sub>	_	4.9	_	S	$I_D = -3 \text{ A}, V_{DS} = -5 \text{ V}$
Input capacitance	Ciss	_	1040	_	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	_	171	_	pF	f = 1MHz
Reverse transfer capacitance	Crss	_	68	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	13	_	ns	$V_{DD} = -30 \text{ V}, I_{D} = -3 \text{ A},$
Rise time	t <sub>r</sub>	_	10	_	ns	$V_{GS} = -10 \text{ V},$
Turn-off delay time	t <sub>d(off)</sub>	_	63	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$
Fall time	t <sub>f</sub>	_	31	_	ns	
Source-drain voltage	V <sub>SD</sub>	_	-1.0	-1.5	V	$I_S = -3 \text{ A}, V_{GS} = 0 \text{ V}$
Thermal resistance	R <sub>th(ch-c)</sub>	_	_	4.17	°C/W	Channel to case
Reverse recovery time	t <sub>rr</sub>	_	50	_	ns	$I_S = -6 \text{ A}, d_{is}/d_t = 100 \text{ A}/\mu\text{s}$

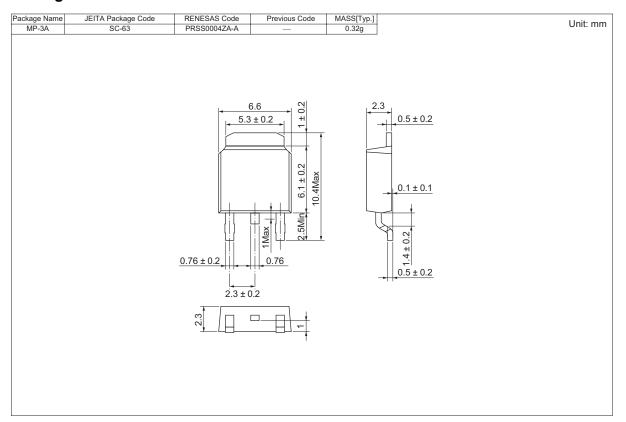
#### **Performance Curves**







## **Package Dimensions**



### **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FX6ASJ-06-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FX6ASJ-06

Note: Please confirm the specification about the shipping in detail.

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